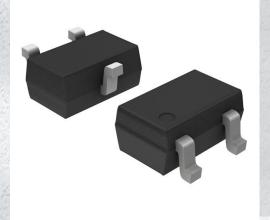


## **SMMBTA56WT3G Datasheet**

www.digi-electronics.com



https://www.DiGi-Electronics.com

DiGi Electronics Part Number SMME

SMMBTA56WT3G-DG

Manufacturer

onsemi

Manufacturer Product Number

SMMBTA56WT3G

Description

TRANS PNP 80V 0.5A SC70-3

**Detailed Description** 

Bipolar (BJT) Transistor PNP 80 V 500 mA 50MHz 15

0 mW Surface Mount SC-70-3 (SOT323)



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



## **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
SMMBTA56WT3G	onsemi
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP	500 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, Ic:
80 V	250mV @ 10mA, 100mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA	100 @ 100mA, 1V
Power - Max:	Frequency - Transition:
150 mW	50MHz
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
SC-70, SOT-323	SC-70-3 (SOT323)
Base Product Number:	
SMMBTA56	

## **Environmental & Export classification**

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0095	

## onsemi

# Driver Transistor PNP Silicon MMBTA56W, SMMBTA56W

### Features

- Moisture Sensitivity Level: 1
- ESD Rating:
  - ♦ Human Body Model 4 kV
  - ♦ Machine Model 400 V
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	-80	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	-80	Vdc
Emitter - Base Voltage	V <sub>EBO</sub>	-4.0	Vdc
Collector Current - Continuous	Ic	-500	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board T <sub>A</sub> = 25°C	$P_{D}$	460	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	272	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

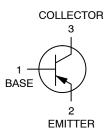
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 Board, 1 oz. Cu, 100 mm<sup>2</sup>.

1



SC-70 (SOT-323) CASE 419 STYLE 3



#### **MARKING DIAGRAM**



FM = Device Code

M = Date Code\*

Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBTA56WT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
SMMBTA56WT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
SMMBTA56WT3G	SC-70 (Pb-Free)	10,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

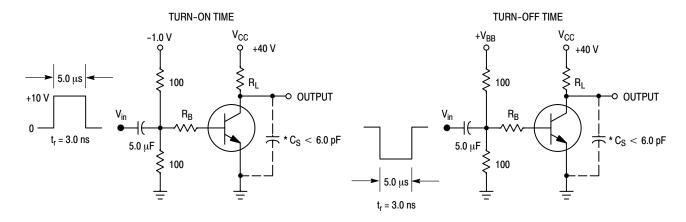
<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### MMBTA56W, SMMBTA56W

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS			1	•
Collector – Emitter Breakdown Voltage (Note 1) $(I_C = -1.0 \text{ mAdc}, I_B = 0)$	V <sub>(BR)</sub> CEO	-80	-	Vdc
Emitter – Base Breakdown Voltage ( $I_E = -100 \mu Adc, I_C = 0$ )	V <sub>(BR)EBO</sub>	-4.0	-	Vdc
Collector Cutoff Current $(V_{CE} = -60 \text{ Vdc}, I_B = 0)$	I <sub>CES</sub>	_	-0.1	μAdc
Collector Cutoff Current $(V_{CB} = -60 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -80 \text{ Vdc}, I_E = 0)$	Ісво	- -	_ _0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain ( $I_C = -10$ mAdc, $V_{CE} = -1.0$ Vdc) ( $I_C = -100$ mAdc, $V_{CE} = -1.0$ Vdc)	h <sub>FE</sub>	100 100	- -	-
Collector – Emitter Saturation Voltage (I <sub>C</sub> = –100 mAdc, I <sub>B</sub> = –10 mAdc)	V <sub>CE(sat)</sub>	_	-0.25	Vdc
Base – Emitter On Voltage (I <sub>C</sub> = –100 mAdc, V <sub>CE</sub> = –1.0 Vdc)	V <sub>BE(on)</sub>	_	-1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS			•	•
Current – Gain – Bandwidth Product (Note 2) (I <sub>C</sub> = –100 mAdc, V <sub>CE</sub> = –1.0 Vdc, f = 100 MHz)	f⊤	50	-	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

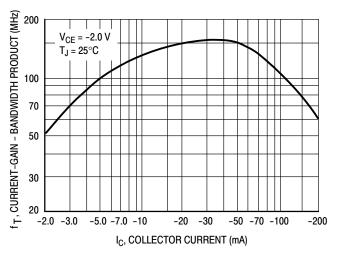


<sup>\*</sup>Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

<sup>2.</sup> f<sub>T</sub> is defined as the frequency at which |h<sub>fe</sub>| extrapolates to unity.

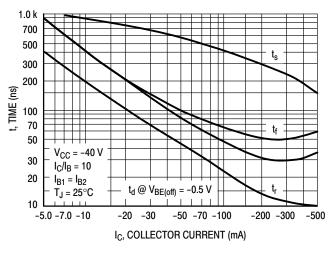
#### MMBTA56W, SMMBTA56W



100 70 50  $C_{ibo}$ C, CAPACITANCE (pF) 30 20  $\mathsf{C}_{\mathsf{obo}}$ 10 7.0 5.0 -0.1 -0.2 -0.5 -1.0 -2.0 -5.0 -10 -50 -100 V<sub>R</sub>, REVERSE VOLTAGE (VOLTS)

Figure 2. Current-Gain — Bandwidth Product

Figure 3. Capacitance



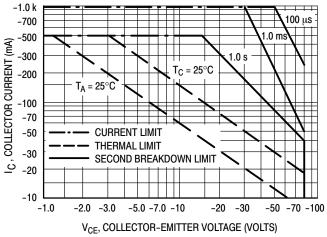
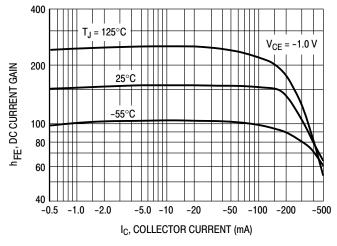


Figure 4. Switching Time

Figure 5. Active-Region Safe Operating Area



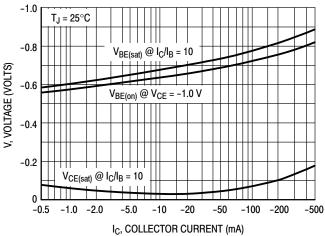
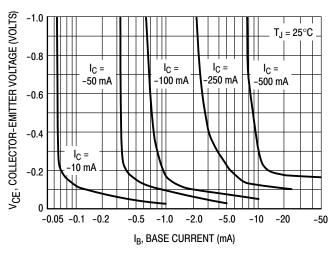


Figure 6. DC Current Gain

Figure 7. "ON" Voltages

#### MMBTA56W, SMMBTA56W



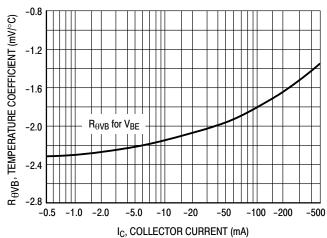


Figure 8. Collector Saturation Region

Figure 9. Base–Emitter Temperature Coefficient



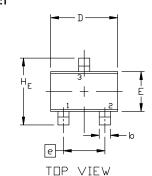
## **MECHANICAL CASE OUTLINE**

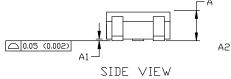
PACKAGE DIMENSIONS

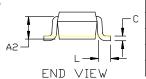


**DATE 11 OCT 2022** 









#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF		0.028 BSC		C
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BS	C	
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



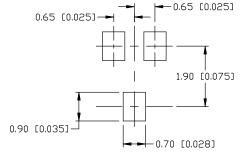


XX = Specific Device Code

= Date Code М

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	<ol><li>CATHODE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>COLLECTOR</li></ol>	3. DRAIN	<ol><li>CATHODE-ANODE</li></ol>	3. ANODE-CATHODE	<ol><li>CATHODE</li></ol>

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